TOSHIBA Transistor Silicon PNP Epitaxial Type

2SA1837

Power Amplifier Applications
Driver Stage Amplifier Applications

- High transition frequency: fT = 70 MHz (typ.)
- Complementary to 2SC4793

Maximum Ratings (Tc = 25°C)

Characteristics		Symbol	Rating	Unit	
Collector-base voltage		V_{CBO}	-230	V	
Collector-emitter voltage		V _{CEO}	-230	V	
Emitter-base voltage		V _{EBO}	-5	V	
Collector current		Ic	-1	Α	
Base current		Ι _Β	-0.1	Α	
Collector power dissipation	Ta = 25°C	Pc	2.0	W	
	Tc = 25°C		20		
Junction temperature		Тј	150	°C	
Storage temperature range		T _{stg}	−55 to 150	°C	

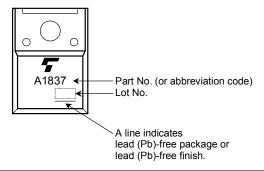
Unit: mm 10±0.3 03.2±0.2 2.7±0.2 0.75±0.15 1. BASE 2. COLLECTOR 3. EMITTER JEDEC JEITA TOSHIBA 2-10R1A

Weight: 1.7 g (typ.)

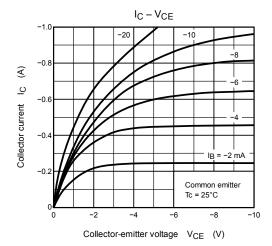
Electrical Characteristics (Tc = 25°C)

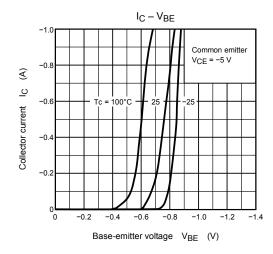
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I _{CBO}	V _{CB} = -230 V, I _E = 0	_	_	-1.0	μΑ
Emitter cut-off current	I _{EBO}	$V_{EB} = -5 \text{ V}, I_{C} = 0$	_	_	-1.0	μΑ
Collector-emitter breakdown voltage	V (BR) CEO	$I_C = -10 \text{ mA}, I_B = 0$	-230	_	_	V
DC current gain	h _{FE}	$V_{CE} = -5 \text{ V, } I_{C} = -100 \text{ mA}$	100	_	320	
Collector-emitter saturation voltage	V _{CE (sat)}	$I_C = -500 \text{ mA}, I_B = -50 \text{ mA}$	_	_	-1.5	V
Base-emitter voltage	V _{BE}	V _{CE} = -5 V, I _C = -500 mA	_	_	-1.0	V
Transition frequency	f _T	V _{CE} = -10 V, I _C = -100 mA	_	70	_	MHz
Collector output capacitance	C _{ob}	V _{CB} = -10 V, I _C = 0, f = 1 MHz	_	30	_	pF

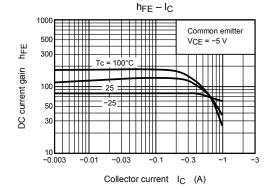
Marking

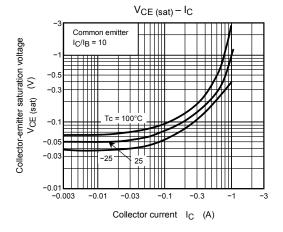


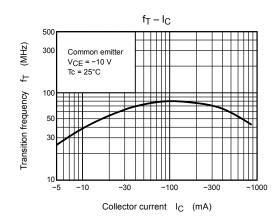
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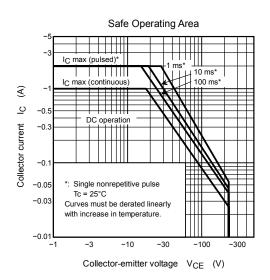












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